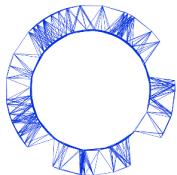


Experiment



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A1-1
Japanese (Japan)

あなたの数字の癖を見るために、次の表に 0 から 9 までの数字を書け。

0	1	2	3	4	5	6	7	8	9

Part A: 回路のディメンジョニング (2.5 点)

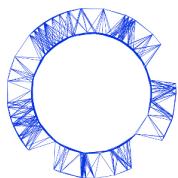
A.1 (0.2 pt)

$$V_{\text{out}} =$$

A.2 (0.5 pt)

#	R_{T1}	R_{T2}	R_{T3}
\bar{R}			
σ_R			

Experiment



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A1-2
Japanese (Japan)

A.3 (0.3 pt)
証明:

A.4 (0.4 pt)

$$R_{\square} = \quad \pm$$

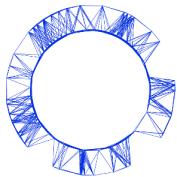
$$\rho_{\text{Carbon film}} = \quad \pm$$

A.5 (0.5 pt)
証明:

測定値:

$$\begin{aligned} R_1 &= \\ R_2 &= \\ \kappa &= \end{aligned}$$

Experiment



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A1-3
Japanese (Japan)

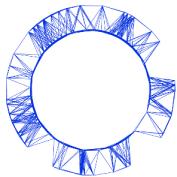
A.6 (0.3 pt)

R_1 Points	R_x	R_y	R_2 Points	R_x	R_y
Z			Z		
A			H		
B			I		
C			J		
D			K		
E			L		
F			M		
G			N		
V			W		

A.7 (0.3 pt)

Points	V_{out}	Points	V_{out}
A		H	
B		I	
C		J	
D		K	
E		L	
F		M	
G		N	
V		W	

Experiment



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A1-4
Japanese (Japan)

Part B: JFET トランジスタの特性曲線 (4.5 点)

B.1 (0.2 pt)

$$I_{DS} =$$

B.2 (0.8 pt)

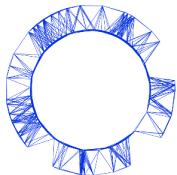
I_{DS} 電流値:

Gate/Drain	Z	H	I	J	K	L	M	N	W
Z									
A									
B									
C									
D									
E									
F									
G									
V									

B.3 (0.2 pt)

$$f =$$

Experiment



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A1-5

Japanese (Japan)

B.4 (1.2 pt)

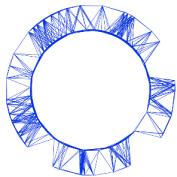
表の空いた列に適切と判断した補正係数を書くこと。

Gate A: $V_{GS} =$ $R_{DS} =$

Gate B: $V_{GS} =$

$$R_{DS} =$$

Experiment



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A1-6

Japanese (Japan)

Japanese (Japan)

B.4 (cont.)

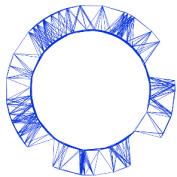
Gate C: $V_{GS} =$

$$R_{\text{DS}} =$$

Gate D: $V_{GS} =$

$$R_{\text{DS}} =$$

Experiment



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A1-7
Japanese (Japan)

Japanese (Japan)

B.4 (cont.)

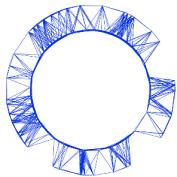
Gate E: $V_{GS} =$

$$R_{\text{DS}} =$$

Gate F: $V_{GS} =$

$$R_{DS} =$$

Experiment



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A1-8

Japanese (Japan)

B.4 (cont.)

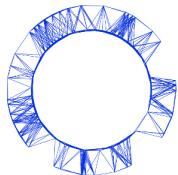
Gate G: $V_{GS} =$

$$R_{\text{DS}} =$$

Gate V: $V_{GS} =$

$$R_{\text{DS}} =$$

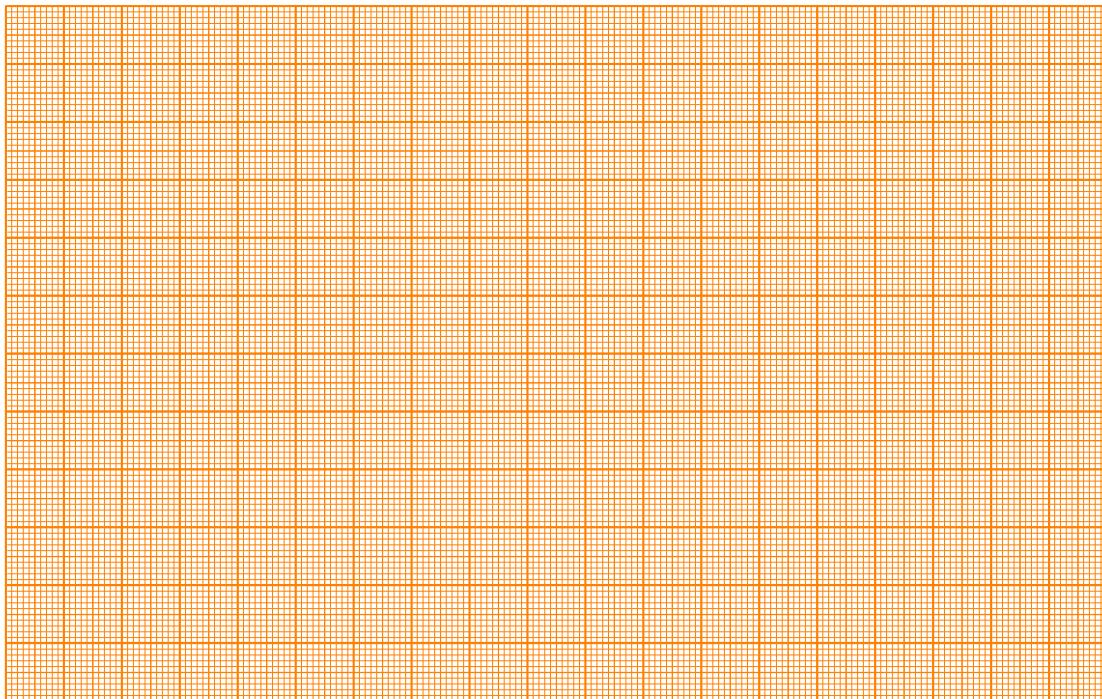
Experiment



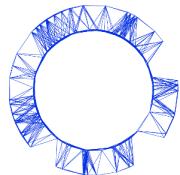
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A1-9
Japanese (Japan)

B.5 (0.5 pt)
出力曲線:



Experiment

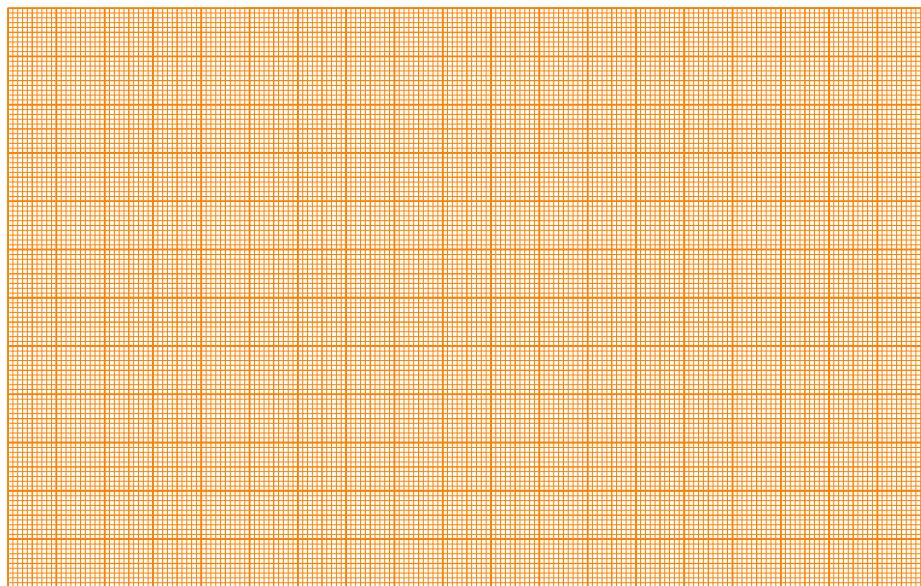


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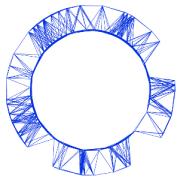
A1-10
Japanese (Japan)

B.6 (0.5 pt)

V_{GS}	R_{DS}



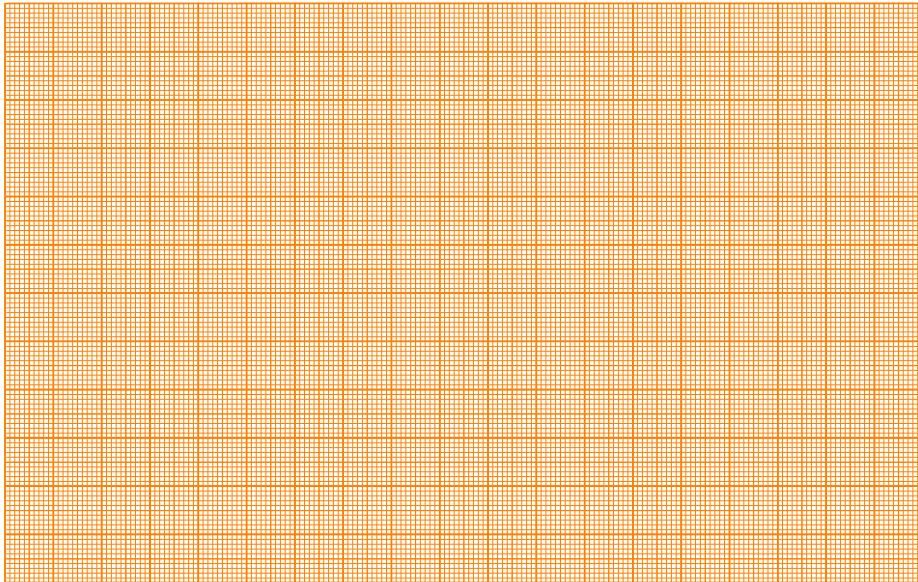
Experiment



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A1-11
Japanese (Japan)

B.7 (0.3 pt)
伝達曲線:



B.8 (0.4 pt)

$$I_{\text{DSS}} =$$

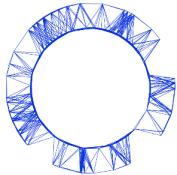
$$V_{\text{P}} =$$

B.9 (0.4 pt)

測定した相互コンダクタンス: $g =$

JFET モデルから計算した相互コンダクタンス: $g =$

Experiment



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A1-12

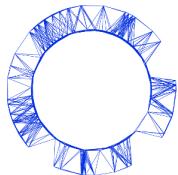
Japanese (Japan)

Part C: 紙薄膜トランジスタ (2.0 点)

C.1 (0.8 pt)

$$I_{\text{closed}} =$$

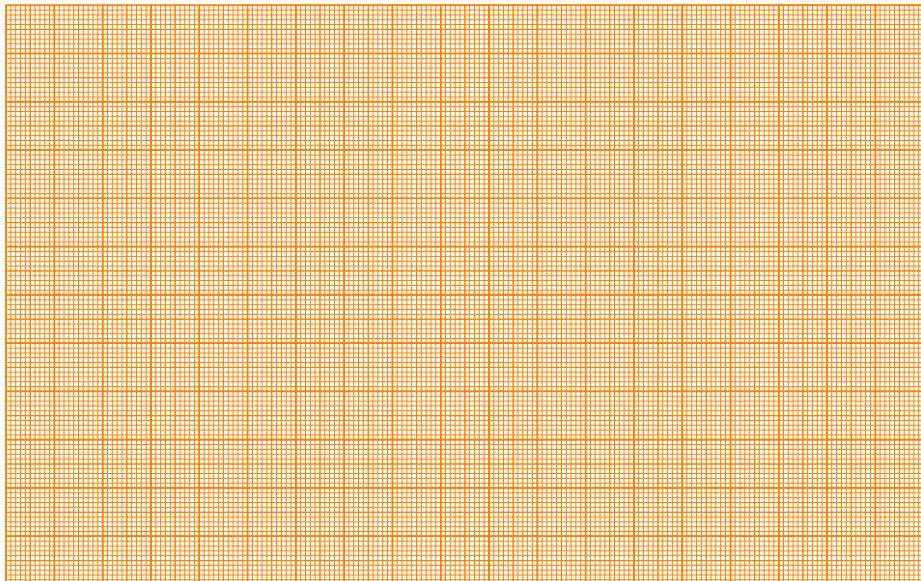
Experiment



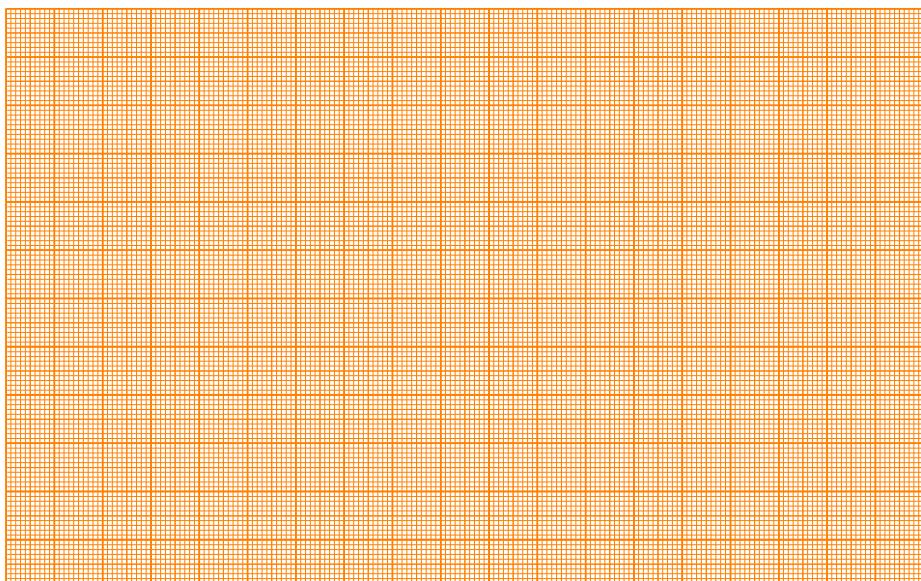
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A1-13
Japanese (Japan)

C.2 (1.2 pt)
グラフ: $I_{DS}(t)$

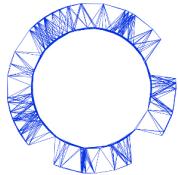


τ_1 を決定するための補助的なグラフ:



$$\tau_1 =$$

Experiment



IPhO 2018
Lisbon, Portugal

A1-14

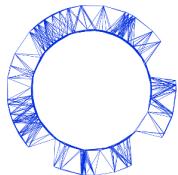
Japanese (Japan)

Part D: 反転回路 (1.0 点)

D.1 (0.5 pt)

$$R_{\mathsf{L}} =$$

Experiment



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A1-15
Japanese (Japan)

D.2 (0.5 pt)
グラフ: $V_{\text{out}}(V_{\text{in}})$

